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TITLE

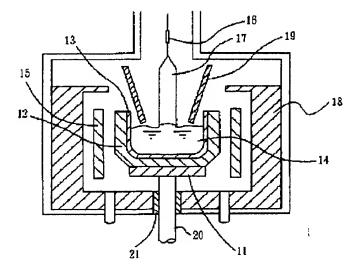
**GRAPHITE MEMBER FOR** 

SEMICONDUCTOR SINGLE CRYSTAL

PULLING UP DEVICE AND

SEMICONDUCTOR SINGLE CRYSTAL

**PULLING UP DEVICE** 



ABSTRACT: PURPOSE: To reduce the evacuating time of a silicon single crystal pulling up device and enhance the single crystal production efficiency by removing a part of the coating layer of a graphite member formed by coating a graphite substrate with IL ceramics such as silicon carbide to expose the graphite substrate.

> CONSTITUTION: A graphite substrate is coated with silicon carbide or silicon nitride or a ceramics contg. silicon carbide and silicon nitride to form the graphite member for a semiconductor single crystal pulling up device, and the substrate is exposed at the rate of 0.03-0.96cm<sup>2</sup> per cm<sup>3</sup> of the member. The member can be applied to all the graphite members such as a crucible 12, heat insulating member 18, heat shielding member 19, crucible supporting member 11 and gas sealing member 21, and the means is more preferably applied to the graphite member positioned above the crucible.

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